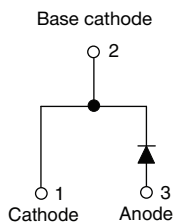


# 650 V Power SiC Gen 3 Merged PIN Schottky Diode, 12 A



TO-220AC 2L



## FEATURES

- Majority carrier diode using Schottky technology on SiC wide band gap material
- Improved  $V_F$  and efficiency by thin wafer technology
- Positive  $V_F$  temperature coefficient for easy paralleling
- Virtually no recovery tail and no switching losses
- Temperature invariant switching behavior
- 175 °C maximum operating junction temperature
- MPS structure for high ruggedness to forward current surge events
- Meets JESD 201 class 1A whisker test
- Solder bath temperature 275 °C maximum, 10 s per JESD 22-B106
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

## LINKS TO ADDITIONAL RESOURCES



3D Models



Application Notes

## PRIMARY CHARACTERISTICS

|                          |             |
|--------------------------|-------------|
| $I_{F(AV)}$              | 12 A        |
| $V_R$                    | 650 V       |
| $V_F$ at $I_F$ at 150 °C | 1.5 V       |
| $T_J$ max.               | 175 °C      |
| $I_R$ at $V_R$ at 175 °C | 5 $\mu$ A   |
| $Q_C$ ( $V_R = 400$ V)   | 34 nC       |
| Package                  | TO-220AC 2L |
| Circuit configuration    | Single      |

## DESCRIPTION / APPLICATIONS

Wide band gap SiC based 650 V Schottky diode, designed for high performance and ruggedness.

Optimum choice for high speed hard switching and efficient operation over a wide temperature range, it is also recommended for all applications suffering from Silicon ultrafast recovery behavior.

Typical applications include AC/DC PFC and DC/DC ultra high frequency output rectification in FBPS and LLC converters.

## MECHANICAL DATA

**Case:** TO-220AC 2L

Molding compound meets UL 94 V-0 flammability rating

Base P/N-M3 - halogen-free, RoHS-compliant

**Terminals:** matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

**Mounting torque:** 10 in-lbs maximum

## ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C unless otherwise specified)

| PARAMETER                                   | SYMBOL               | TEST CONDITIONS                                    | VALUES      | UNITS            |
|---------------------------------------------|----------------------|----------------------------------------------------|-------------|------------------|
| Peak repetitive reverse voltage             | $V_{RRM}$            |                                                    | 650         | V                |
| Average rectified forward current           | $I_{F(AV)}$          | $T_C = 125$ °C (DC)                                | 12          | A                |
| DC blocking voltage                         | $V_{DC}$             |                                                    | 650         | V                |
| Repetitive peak forward current             | $I_{FRM}$            | $T_C = 25$ °C, $f = 50$ Hz, square wave, DC = 25 % | 48          | A                |
| Non-repetitive peak forward surge current   | $I_{FSM}$            | $T_C = 25$ °C, $t_p = 10$ ms, half sine wave       | 83          | A                |
|                                             |                      | $T_C = 110$ °C, $t_p = 10$ ms, half sine wave      | 74          |                  |
| Power dissipation                           | $P_{tot}^{(1)}$      | $T_C = 25$ °C                                      | 72          | W                |
|                                             |                      | $T_C = 110$ °C                                     | 32          |                  |
| $I^2t$ value                                | $\int i^2 dt$        | $T_C = 25$ °C                                      | 34.5        | A <sup>2</sup> s |
|                                             |                      | $T_C = 110$ °C                                     | 27          |                  |
| Operating junction and storage temperatures | $T_J^{(2)}, T_{Stg}$ |                                                    | -55 to +175 | °C               |

## Notes

(1) Based on maximum  $R_{th}$

(2) The heat generated must be less than the thermal conductivity from junction-to-ambient:  $dP_D/dT_J < 1/R_{thJA}$

| <b>ELECTRICAL SPECIFICATIONS</b> ( $T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise specified) |        |                                                             |      |      |      |               |
|---------------------------------------------------------------------------------------------------|--------|-------------------------------------------------------------|------|------|------|---------------|
| PARAMETER                                                                                         | SYMBOL | TEST CONDITIONS                                             | MIN. | TYP. | MAX. | UNITS         |
| Forward voltage                                                                                   | $V_F$  | $I_F = 12\text{ A}$                                         | -    | 1.3  | 1.5  | V             |
|                                                                                                   |        | $I_F = 12\text{ A}, T_J = 150\text{ }^{\circ}\text{C}$      | -    | 1.50 | 1.85 |               |
|                                                                                                   |        | $I_F = 12\text{ A}, T_J = 175\text{ }^{\circ}\text{C}$      | -    | 1.58 | -    |               |
| Reverse leakage current                                                                           | $I_R$  | $V_R = V_R\text{ rated}$                                    | -    | 0.8  | 65   | $\mu\text{A}$ |
|                                                                                                   |        | $V_R = V_R\text{ rated}, T_J = 150\text{ }^{\circ}\text{C}$ | -    | 3    | 150  |               |
|                                                                                                   |        | $V_R = V_R\text{ rated}, T_J = 175\text{ }^{\circ}\text{C}$ | -    | 5    | -    |               |
| Total capacitance                                                                                 | C      | $V_R = 1\text{ V}, f = 1\text{ MHz}$                        | -    | 535  | -    | pF            |
|                                                                                                   |        | $V_R = 400\text{ V}, f = 1\text{ MHz}$                      | -    | 54   | -    |               |
| Total capacitive charge                                                                           | $Q_C$  | $V_R = 400\text{ V}, f = 1\text{ MHz}$                      | -    | 34   | -    | nC            |

| <b>THERMAL - MECHANICAL SPECIFICATIONS</b> ( $T_A = 25\text{ }^{\circ}\text{C}$ unless otherwise specified) |            |                 |      |           |      |                      |
|-------------------------------------------------------------------------------------------------------------|------------|-----------------|------|-----------|------|----------------------|
| PARAMETER                                                                                                   | SYMBOL     | TEST CONDITIONS | MIN. | TYP.      | MAX. | UNITS                |
| Thermal resistance, junction-to-case                                                                        | $R_{thJC}$ |                 | -    | 1.6       | 2.1  | $^{\circ}\text{C/W}$ |
| Marking device                                                                                              |            |                 |      | 3C12ET07T |      |                      |

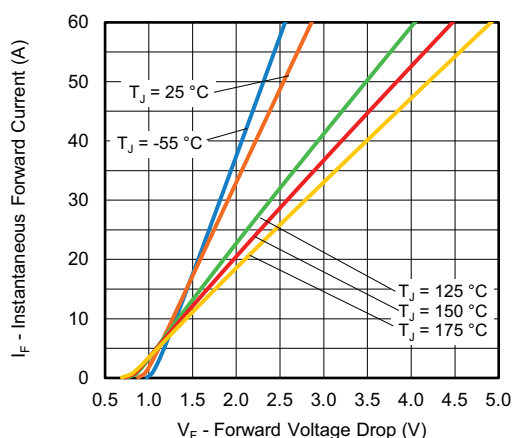


Fig. 1 - Typical Forward Voltage Drop Characteristics

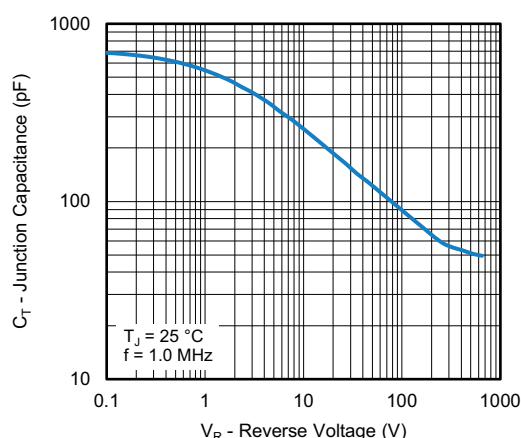


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

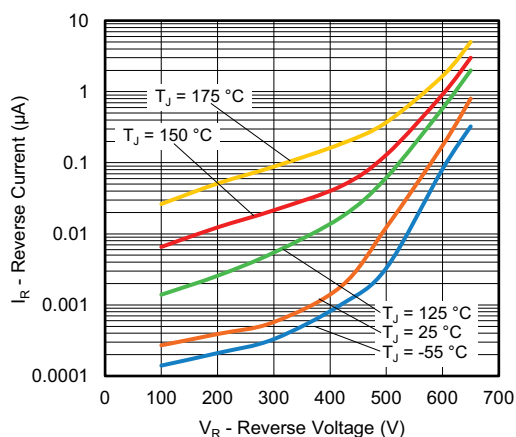


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

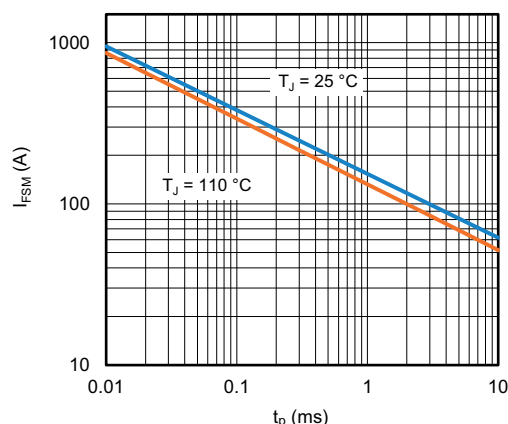


Fig. 4 - Non-Repetitive Peak Forward Surge Current vs. Pulse Duration (Square Wave)

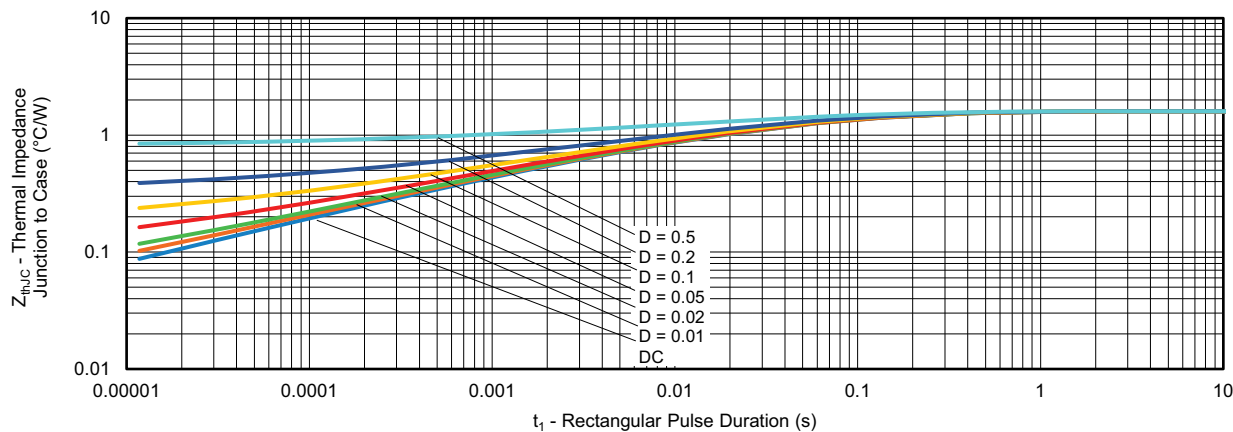
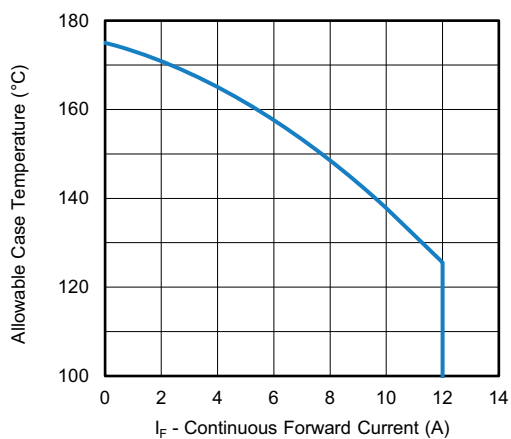

Fig. 5 - Typical Thermal Impedance  $Z_{thJC}$  Characteristics


Fig. 6 - Maximum Allowable Case Temperature vs. Average Forward Current

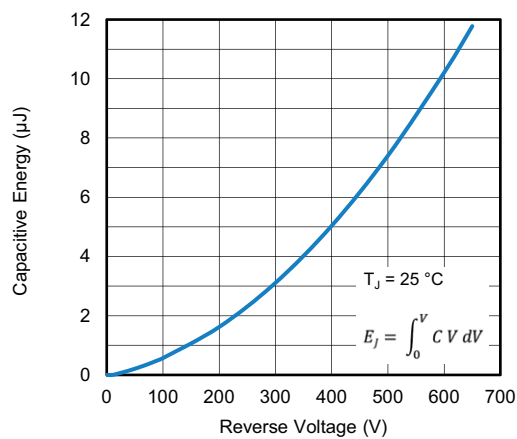


Fig. 8 - Typical Capacitive Energy vs. Reverse Voltage

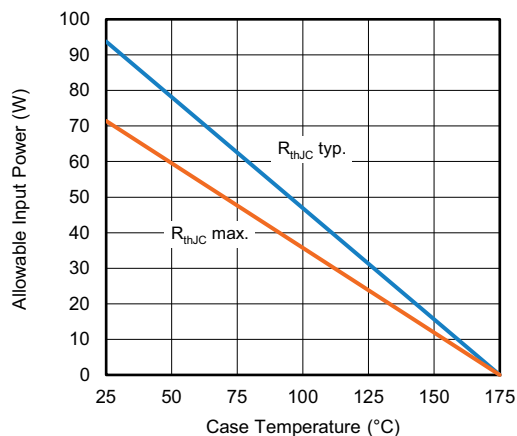


Fig. 7 - Forward Power Loss Characteristics

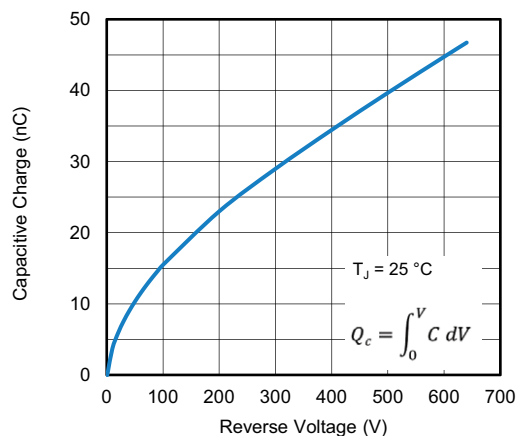


Fig. 9 - Typical Capacitive Charge vs. Reverse Voltage

**ORDERING INFORMATION TABLE**

|             |                                                                                              |    |    |   |   |    |   |     |
|-------------|----------------------------------------------------------------------------------------------|----|----|---|---|----|---|-----|
| Device code | VS-                                                                                          | 3C | 12 | E | T | 07 | T | -M3 |
|             | 1                                                                                            | 2  | 3  | 4 | 5 | 6  | 7 | 8   |
| 1           | - Vishay Semiconductors product                                                              |    |    |   |   |    |   |     |
| 2           | - 3C = SiC diode, Generation 3                                                               |    |    |   |   |    |   |     |
| 3           | - Current rating (12 = 12 A)                                                                 |    |    |   |   |    |   |     |
| 4           | - E = single diode                                                                           |    |    |   |   |    |   |     |
| 5           | - Package TO-220                                                                             |    |    |   |   |    |   |     |
| 6           | - Voltage rating: (07 = 650 V)                                                               |    |    |   |   |    |   |     |
| 7           | - T = true 2 pin                                                                             |    |    |   |   |    |   |     |
| 8           | - Environmental digit:<br>-M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free |    |    |   |   |    |   |     |

| ORDERING INFORMATION |               |                          |
|----------------------|---------------|--------------------------|
| PREFERRED P/N        | BASE QUANTITY | PACKAGING DESCRIPTION    |
| VS-3C12ET07T-M3      | 50/tube       | Antistatic plastic tubes |

| LINKS TO RELATED DOCUMENTS |                                                                        |
|----------------------------|------------------------------------------------------------------------|
| Dimensions                 | <a href="http://www.vishay.com/doc?96069">www.vishay.com/doc?96069</a> |
| Part marking information   | <a href="http://www.vishay.com/doc?95391">www.vishay.com/doc?95391</a> |





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